## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet



## FMMT\* % TRANSISTOR (BDB)





SOT - 23

1. BASE

- 2. EMITTER
- 3. COLLECTOR

#### **FEATURE**

- Extremely low saturation voltage
- Complementary PNÚ type: FMMTÏ 18

#### **APPLICATION**

- Gate Driving MOSFETs and IGBTs
- DC-DC converters
- Charging circuit
- Power switches

MARKING: \*18

#### MAXIMUM RATINGS (T<sub>a</sub>=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
<b>V</b> сво	Collector-Base Voltage		V
Vceo	Collector-Emitter Voltage	20	V
<b>V</b> EBO	Emitter-Base Voltage	5	V
lв	Base Current	0.5	Α
Ic	Collector Current -Continuous	2.5	Α
Pc	Total Collector Dissipation	350	mW
R <sub>OJA</sub>	Thermal Resistance from Junction to Ambient	357	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	℃



**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)** 

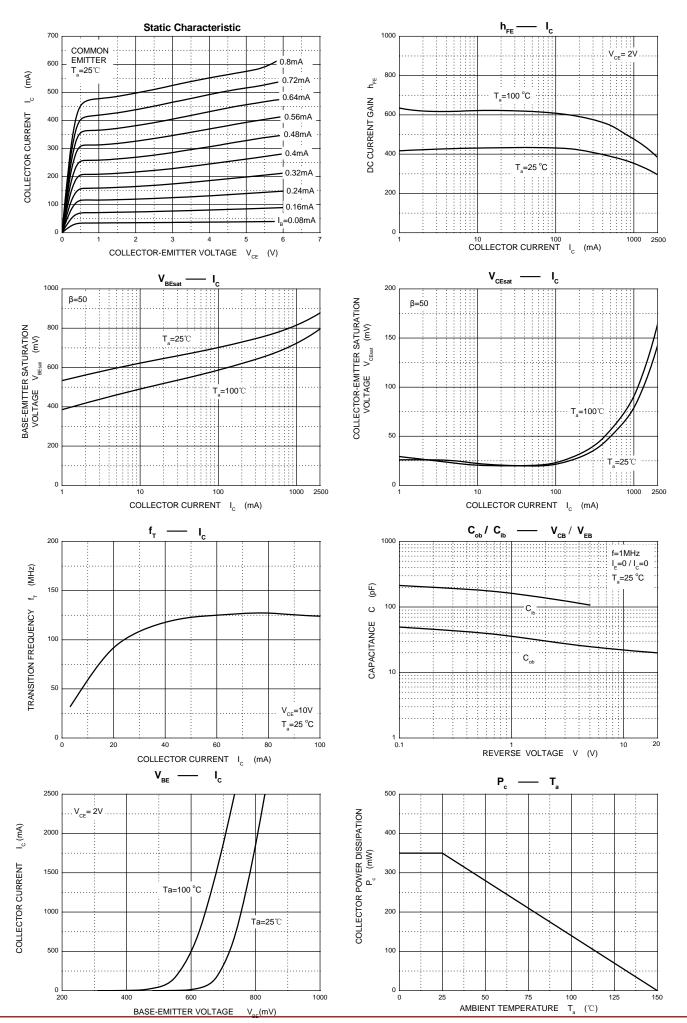
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA,I <sub>E</sub> =0	20			V
Collector-emitter breakdown voltage (note 1)	V <sub>(BR)CEO</sub>	I <sub>C</sub> =10mA,I <sub>B</sub> =0	20			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA ,I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =16V,I <sub>E</sub> =0			100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V,I <sub>C</sub> =0			100	nA
	h <sub>FE(1)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =10mA	200			
DC ourrent gain (note 1)	h <sub>FE(2)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =0.2A	300			
DC current gain (note 1)	h <sub>FE(3)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =2A	200			
	h <sub>FE(4)</sub>	V <sub>CE</sub> =2V, I <sub>C</sub> =4A	100			
	V <sub>CE(sat)1</sub>	I <sub>C</sub> =0.1A,I <sub>B</sub> =10mA			15	mV
Collector-emitter saturation voltage (note 1)	V <sub>CE(sat)2</sub>	I <sub>C</sub> =1A,I <sub>B</sub> =10mA			150	mV
	V <sub>CE(sat)3</sub>	I <sub>C</sub> =2 <b>Ĕ</b> A,I <sub>B</sub> =Í 0mA			200	mV
Base-emitter saturation voltage (note 1)	V <sub>BE(sat)</sub>	I <sub>C</sub> =2 <u>H</u> A,I <sub>B</sub> =50mA			1	V
Base-emitter on voltage (note 1)	V <sub>BE(on)</sub>	I <sub>C</sub> =2Ě A, V <sub>CE</sub> =2V			1	V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz			30	pF
Turn-on time	t <sub>(on)</sub>	V <sub>CC</sub> =10V, I <sub>C</sub> =1A, I <sub>B1</sub> =-I <sub>B2</sub> =10mA		170		ns
Turn-off time	t <sub>(off)</sub>	VCC=1UV, IC=1A, IB1=-IB2=1UIIIA		400		ns
Transition frequency	f⊤	V <sub>CE</sub> =10V,I <sub>C</sub> =50mA, f=100MHz 100				MHz

#### Notes:

1. Pulse test: Pulse width≤300µs,duty cycle≤2.0%.

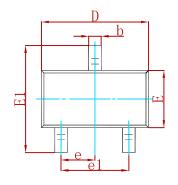
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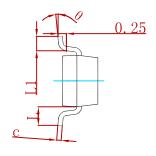


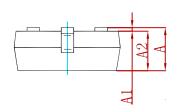




#### **PACKAGE MECHANICAL DATA**

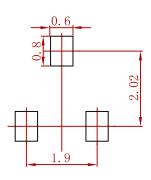






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
FMMT618	SOT-23	3000



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